

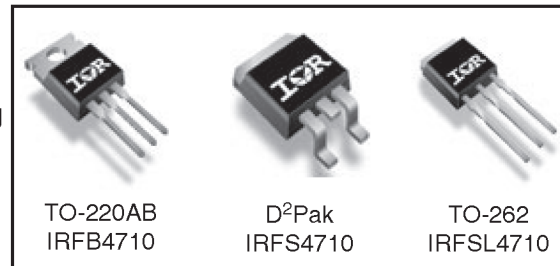
Applications

- High frequency DC-DC converters
- Motor Control
- Uninterruptible Power Supplies
- Lead-Free

V _{DSS}	R _{DS(on)} max	I _D
100V	0.014Ω	75A

Benefits

- Low Gate-to-Drain Charge to Reduce Switching Losses
- Fully Characterized Capacitance Including Effective C_{OSS} to Simplify Design, (See App. Note AN1001)
- Fully Characterized Avalanche Voltage and Current



Absolute Maximum Ratings

	Parameter	Max.	Units
I _D @ T _C = 25°C	Continuous Drain Current, V _{GS} @ 10V	75	A
I _D @ T _C = 100°C	Continuous Drain Current, V _{GS} @ 10V	53	
I _{DM}	Pulsed Drain Current ①	300	
P _D @ T _A = 25°C	Power Dissipation ②	3.8	W
P _D @ T _C = 25°C	Power Dissipation	200	W/°C
	Linear Derating Factor	1.4	
V _{GS}	Gate-to-Source Voltage	± 20	V
dv/dt	Peak Diode Recovery dv/dt ③	8.2	V/ns
T _J	Operating Junction and	-55 to + 175	°C
T _{STG}	Storage Temperature Range		
	Soldering Temperature, for 10 seconds	300 (1.6mm from case)	
	Mounting torque, 6-32 or M3 screw④	10 lbf•in (1.1N•m)	

Thermal Resistance

	Parameter	Typ.	Max.	Units
R _{θJC}	Junction-to-Case	—	0.74	°C/W
R _{θCS}	Case-to-Sink, Flat, Greased Surface ⑤	0.50	—	
R _{θJA}	Junction-to-Ambient⑥	—	62	
R _{θJA}	Junction-to-Ambient⑦	—	40	

Notes ① through ⑦ are on page 11

IRFB/IRFS/IRFL4710PbF

International
IR Rectifier

Static @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	100	—	—	V	$V_{GS} = 0V, I_D = 250\mu A$
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	0.11	—	V/ $^\circ\text{C}$	Reference to $25^\circ\text{C}, I_D = 1\text{mA}$
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	0.011	0.014	Ω	$V_{GS} = 10V, I_D = 45A$ ④
$V_{GS(th)}$	Gate Threshold Voltage	3.5	—	5.5	V	$V_{DS} = V_{GS}, I_D = 250\mu A$
I_{DSS}	Drain-to-Source Leakage Current	—	—	1.0	μA	$V_{DS} = 95V, V_{GS} = 0V$
		—	—	250		$V_{DS} = 80V, V_{GS} = 0V, T_J = 150^\circ\text{C}$
I_{GSS}	Gate-to-Source Forward Leakage	—	—	100	nA	$V_{GS} = 20V$
	Gate-to-Source Reverse Leakage	—	—	-100		$V_{GS} = -20V$

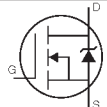
Dynamic @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
g_{fs}	Forward Transconductance	35	—	—	S	$V_{DS} = 50V, I_D = 45A$
Q_g	Total Gate Charge	—	110	170	nC	$I_D = 45A$
Q_{gs}	Gate-to-Source Charge	—	43	—		$V_{DS} = 50V$
Q_{gd}	Gate-to-Drain ("Miller") Charge	—	40	—		$V_{GS} = 10V,$
$t_{d(on)}$	Turn-On Delay Time	—	35	—	ns	$V_{DD} = 50V$
t_r	Rise Time	—	130	—		$I_D = 45A$
$t_{d(off)}$	Turn-Off Delay Time	—	41	—		$R_G = 4.5\Omega$
t_f	Fall Time	—	38	—		$V_{GS} = 10V$ ④
C_{iss}	Input Capacitance	—	6160	—	pF	$V_{GS} = 0V$
C_{oss}	Output Capacitance	—	440	—		$V_{DS} = 25V$
C_{rss}	Reverse Transfer Capacitance	—	250	—		$f = 1.0\text{MHz}$
C_{oss}	Output Capacitance	—	1580	—		$V_{GS} = 0V, V_{DS} = 1.0V, f = 1.0\text{MHz}$
C_{oss}	Output Capacitance	—	280	—		$V_{GS} = 0V, V_{DS} = 80V, f = 1.0\text{MHz}$
$C_{oss \text{ eff.}}$	Effective Output Capacitance	—	430	—		$V_{GS} = 0V, V_{DS} = 0V \text{ to } 80V$ ⑤

Avalanche Characteristics

	Parameter	Typ.	Max.	Units
E_{AS}	Single Pulse Avalanche Energy ②	—	190	mJ
I_{AR}	Avalanche Current ①	—	45	A
E_{AR}	Repetitive Avalanche Energy ①	—	20	mJ

Diode Characteristics

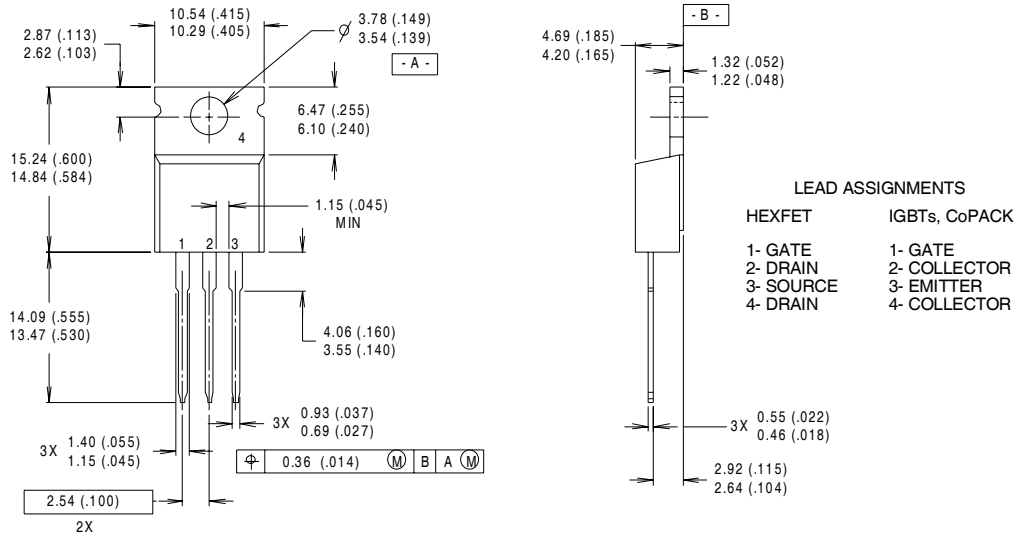
	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	—	—	75	A	MOSFET symbol showing the integral reverse p-n junction diode. 
I_{SM}	Pulsed Source Current (Body Diode) ①⑥	—	—	300		
V_{SD}	Diode Forward Voltage	—	—	1.3	V	$T_J = 25^\circ\text{C}, I_S = 45A, V_{GS} = 0V$ ④
t_{rr}	Reverse Recovery Time	—	74	110	ns	$T_J = 25^\circ\text{C}, I_F = 45A$
Q_{rr}	Reverse Recovery Charge	—	180	260	nC	$di/dt = 100A/\mu s$ ④
t_{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by L_S+L_D)				

IRFB/IRFS/IRFL4710PbF

International
IR Rectifier

TO-220AB Package Outline

Dimensions are shown in millimeters (inches)



NOTES:

- 1 DIMENSIONING & TOLERANCING PER ANSI Y14.5M, 1982.
- 2 CONTROLLING DIMENSION : INCH

- 3 OUTLINE CONFORMS TO JEDEC OUTLINE TO-220AB.
- 4 HEATSINK & LEAD MEASUREMENTS DO NOT INCLUDE BURRS.

TO-220AB Part Marking Information

EXAMPLE: THIS IS AN IRF1010
LOT CODE 1789
ASSEMBLED ON WW 19, 1997
IN THE ASSEMBLY LINE "C"

Note: "P" in assembly line position indicates "Lead-Free"

